

TCT and CCE measurements for 9 MeV and 24 GeV/c irradiated n-type MCz-Si pad detectors

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N-type MCz-Si pad detectors have been irradiated by 9 MeV and 24 GeV/c protons up to 1×10^{16} neff/cm² fluence. The samples have been characterized by Transient Current Technique (TCT) operating with 670nm laser and Charge Collection Efficiency (CCE) measurements performed by 1060nm IR laser. Low and high energy proton irradiation results are compared and charge collection of MCz-Si detectors is discussed.

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